

RJK4014DPK

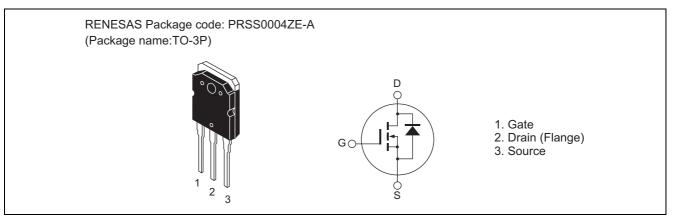
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1576-0100 Rev.1.00 Aug 08, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	400	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	24	А
Drain peak current	Note1 I _{D (pulse)}	72	А
Body-drain diode reverse drain current	I _{DR}	24	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	72	А
Avalanche current	I _{AP} ^{Note3}	8	А
Avalanche energy	E _{AR} ^{Note3}	3.65	mJ
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	400		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}		0.20	0.24	Ω	$I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1800	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	220	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	29	_	pF	
Turn-on delay time	t _{d(on)}	_	35	—	ns	I _D = 12 A
Rise time	tr	_	63	_	ns	$V_{GS} = 10 V$ $R_L = 16.7 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	93	_	ns	
Fall time	t _f	_	49	_	ns	
Total gate charge	Qg	—	47	_	nC	V _{DD} = 320 V
Gate to source charge	Qgs	_	10	_	nC	V _{GS} = 10 V I _D = 24 A
Gate to drain charge	Qgd	—	21	_	nC	
Body-drain diode forward voltage	V _{DF}	—	0.95	1.60	V	$I_F = 24 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	_	310	_	ns	$I_F = 24$ A, $V_{GS} = 0$ $di_F/dt = 100$ A/µs

Notes: 4. Pulse test

Package Dimensions

Package Name TO-3P	JEITA Package Code SC-65	RENESAS Code	Previous Code	MASS[Typ.]	
10-3P	SC-65	PRSS0004ZE-A 15.6 ± 0.3	TO-3P/TO-3PV	5.0g 4.8 ± 0.2 1.5 2.8 0.6 ± 0.2	Unit: mm
	<u>5.45 ± 0</u>		<u>.0</u> <u>.0</u> <u>.5.45 ± 0.5</u>		

Ordering Information

Part No.	Quantity	Shipping Container
RJK4014DPK-00-T0	360 pcs	Box (Tube)

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